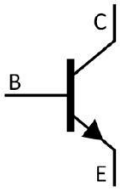


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SOT-23 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

600mA
 Collector currents up to 600 mA.

General purpose amplifier.



PIN 1 Base PIN 2 Emitter PIN 3 Collector

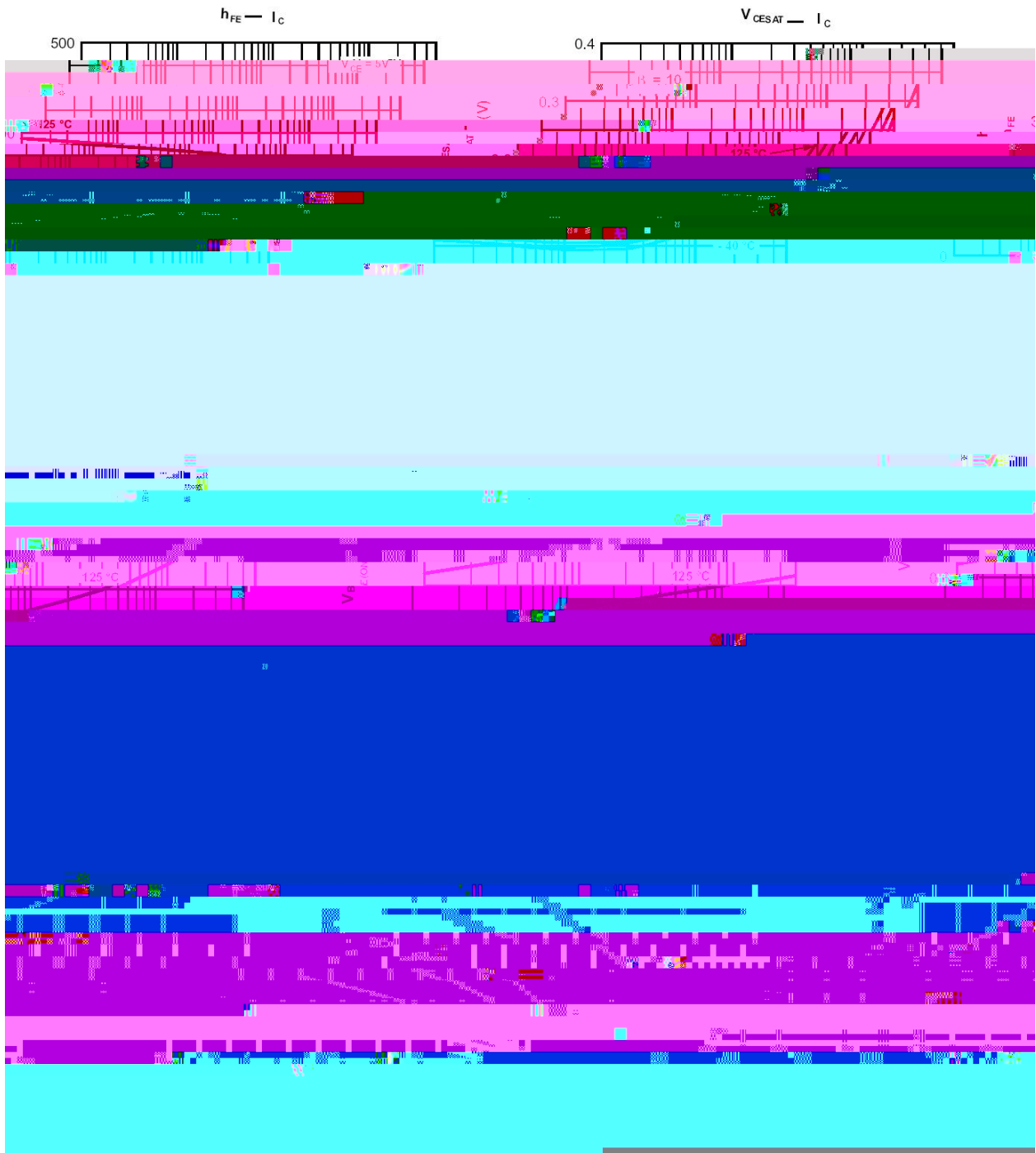
h_{FE} Range	100 300
Marking	H1P

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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	75	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

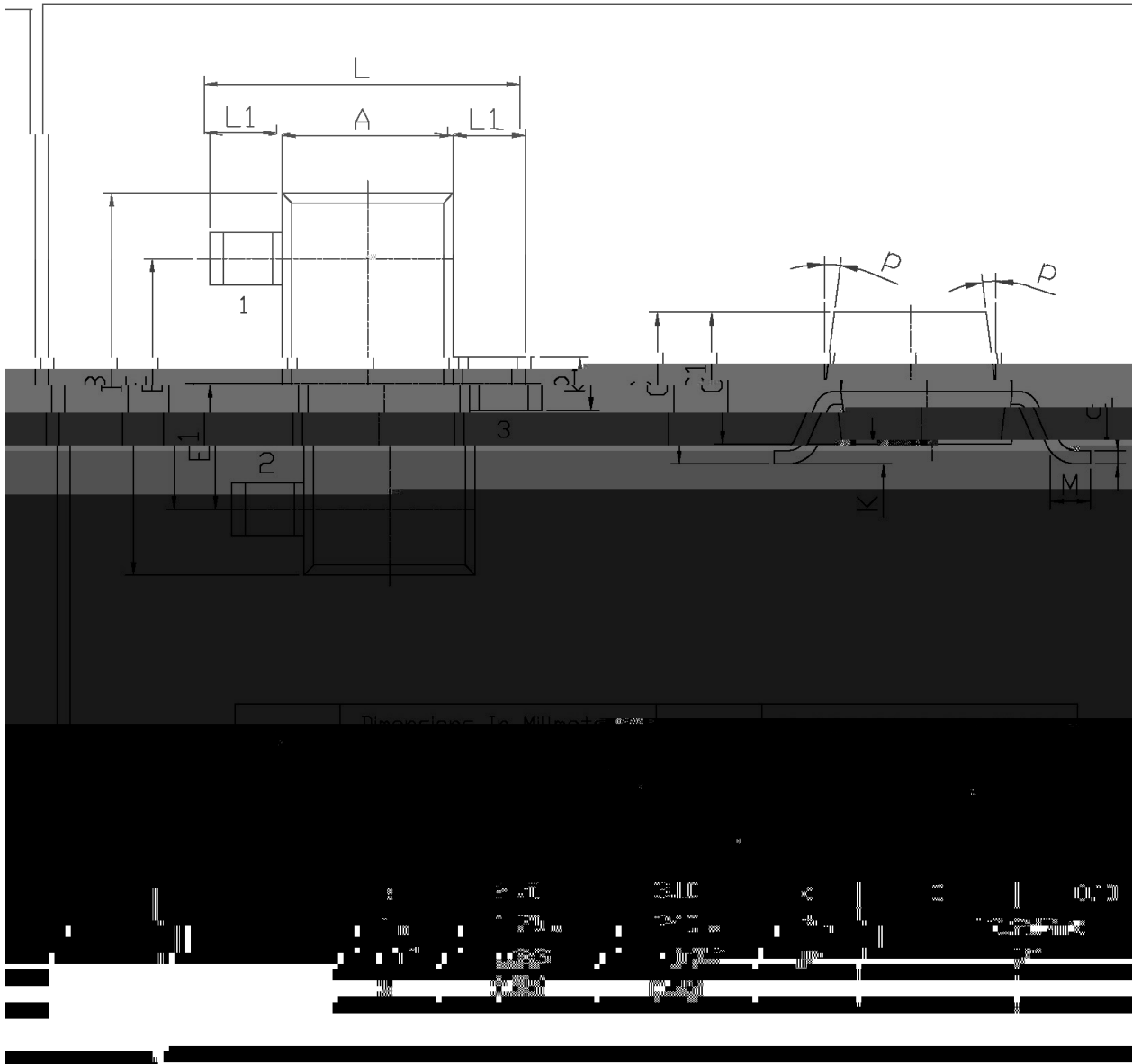
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10\text{ A}$ $I_E=0$	75			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10\text{mA}$ $I_B=0$	40			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\text{ A}$ I_C				

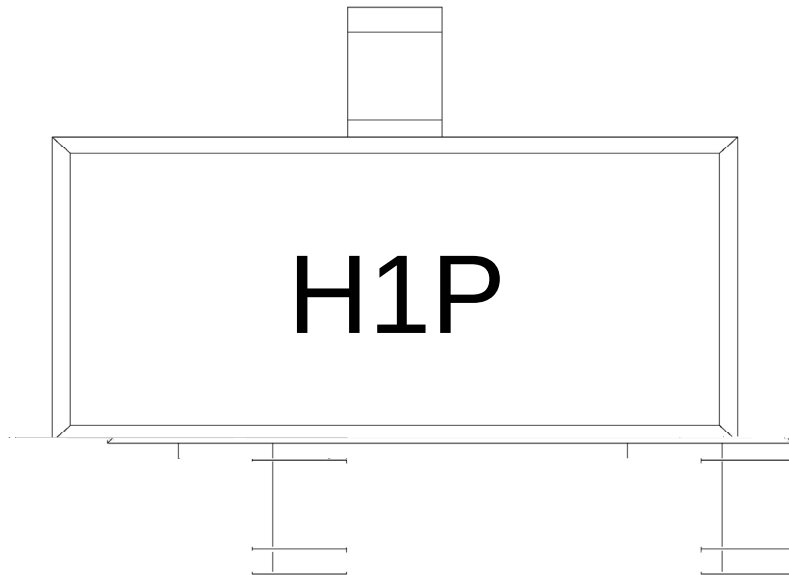
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SUT -23

单位: 湖南





H

1P

Note:

H Company Code

1P Product Type Code

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